

10/767627

Inventor: MATSUBARA, KEN, et al

Status: 30 - DOCKETED NEW CASE - READY FOR EXAMINATION

Title: NONVOLATILE MEMORY AND METHOD OF RESTORING OF FAILURE MEMORY CELL

Examiner: NGUYEN, NAM

GAU: 2824  
Classification: 365/185.240

Incoming tab report (11 items, not sorted)

Seq	Status	Doc Code	Document Type	Receipt Date	Pages	Annotations
7	7	TRNA	Transmittal letter	01/30/2004	4	
7	7	SPEC	Specification	01/30/2004	32	
7	7	CLM	Claims	01/30/2004	6	
7	7	ABST	Abstract	01/30/2004	1	
7	7	OATH	Oath or Declaration filed	01/30/2004	4	
7	7	DRW	Drawings	01/30/2004	16	
7	7	APE	Preliminary Amendment	01/30/2004	1	
7	7	CLM	Claims	01/30/2004	7	
7	7	REM	Applicant Arguments or Remarks Made in an Amendment	01/30/2004	1	
7	7	IDS	Information Disclosure Statement (IDS) Filed	01/30/2004	2	CONSIDERED 9/9/05
7	7	FRPR	Foreign Priority Papers Filed	01/30/2004	49	

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2233	365/185.18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:20
L2	637	1 and (restor\$4 or refresh\$4 or rewrit\$4 or recharge\$4 or re-stor\$4 or re-fresh\$4 or re-writ\$4 or re-charg\$4 or (write adj back) or write-back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:20
L3	637	2 and (restor\$4 or refresh\$4 or rewrit\$4 or recharge\$4 or re-stor\$4 or re-fresh\$4 or re-writ\$4 or re-charg\$4 or (write adj back) or write-back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:22
L4	204	3 and fail\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:20
L5	50	4 and unselect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:20
L6	2350	365/185.33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:22
L7	875	6 and (restor\$4 or refresh\$4 or rewrit\$4 or recharge\$4 or re-stor\$4 or re-fresh\$4 or re-writ\$4 or re-charg\$4 or (write adj back) or write-back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:20
L8	875	7 and (restor\$4 or refresh\$4 or rewrit\$4 or recharge\$4 or re-stor\$4 or re-fresh\$4 or re-writ\$4 or re-charg\$4 or (write adj back) or write-back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:20
L9	357	8 and fail\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:20
L10	41	9 and unselect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:23

L11	195	matsubara-ken.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:21
L12	246	tamura-takayuki.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:22
L13	34	fujisawa-tomoyuki.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:22
L14	1912	365/185.29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:22
L15	718	14 and (restor\$4 or refresh\$4 or rewrit\$4 or recharge\$4 or re-stor\$4 or re-fresh\$4 or re-writ\$4 or re-charg\$4 or (write adj back) or write-back)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:22
L16	218	15 and defect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:23
L17	34	16 and unselect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:23
L18	1	((second adj operation) and (failing adj memory) and (nonvolatile adj memory adj element) and (threshold adj voltage)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:26
S1	84408	flash adj memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 13:59
S2	107794	(nonvolatile or non-volatile) adj memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:00

S3	105829	threshold adj voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:00
S4	29569	S1 and S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:00
S5	5102	S3 and S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:00
S6	564	S5 and restor\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:01
S7	467177	(electrically adj3 memory) or (erasable adj3 memory) or (\$1eprom) or (flash or non-volatile or (non adj volatile) adj3 (memory or cell)) or ((non adj volatile) or nonvolatile or non-volatile) adj3 (memory or cell) or nvm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:02
S8	564	S6 and S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:03
S9	551862	restor\$4 or refresh\$4 or rewrit\$4 or recharg\$4 or re-stor\$4 or re-fresh\$4 or re-writ\$4 or re-charg\$4 or (write adj back) or write-back	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:19
S10	2075	S5 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:03
S11	723	S10 and fail\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:19
S12	160	S11 and unselect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:19

S13	1179	365/185.24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:18
S14	976	S3 and S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:06
S15	926	S7 and S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:06
S16	350	S9 and S15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:06
S17	112	S16 and fail\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:06
S18	31113	(nonvolatile or (non-volatile) or (non adj volatile) adj3 memory)[ti]	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 14:07